

REMARKS/ARGUMENTS

Support for the amendment to Claim 11 is found in original Claim 1, and e.g., the several original Figures. Claim 14, indicated as allowable, has been placed in independent form. New Claims 21 and 22 are supported at specification page 1, lines 8-9. New Claims 23 and 26 limit Claim 11 by requiring one of the alternative first stages listed in Claim 11 (i.e., bonding/implanting and implanting/bonding). New Claims 24 and 25, and 27 and 28, parallel Claims 12 and 13. New Claims 29 and 30 parallel new Claims 23 and 26 but use “consisting of” language. No new matter has been entered.

Applicants greatly appreciate the indication that Claims 14-18 would be allowable if rewritten in independent form to include all the limitations of any intervening claims. As noted by the above amendment, Claim 14 has been placed in independent form, and Claims 15-18 depend, ultimately, from Claim 14. Thus, these claims are in condition for allowance.

With regard to Claim 11 and the claims dependent thereon, these claims have been amended so as to require a specific order of the listed steps. That is, according to these claims the steps must be executed in the order listed: bonding/implanting or implanting/bonding followed by depositing and then fracturing.¹ In addition, Claim 11 has been amended to make more clear the fact that the layer of the third material is a self-supporting layer. See, for example, specification page 8, lines 10-13, where a self-supporting layer of silicon oxide that is 4 μm thick is described.

These amendments to the claims remove any arguable relation between the present invention and Eriksen (U.S. '158). For example, even if Eriksen were considered to disclose certain individual steps of Applicants' claims, the reference cannot be said to fairly suggest Applicants' specifically claimed process in the order required. For example, in Eriksen ion

¹ Note that the “first step” in Claim 11 actually requires two things, and that Claim 11 lists two alternative choices for this “first step”: a bonding followed by implanting “first step” and an implanting followed by bonding “first step.” Claims 23 and 26, and 29 and 30, require one or the other of these “first steps.”

bombardment occurs after formation of oxide layer 6 over SiC layer 4. See column 4, lines 30-45, as depicted in Figures 1C and 1D:

FIG. 1C

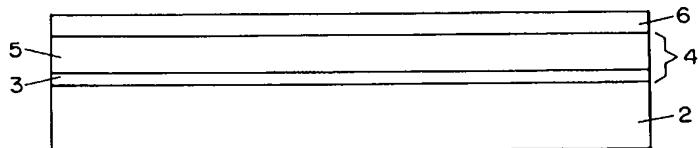
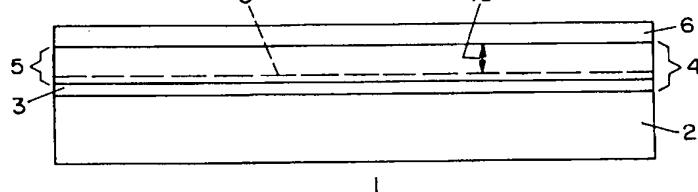


FIG. 1D



In addition, this oxide layer 6 in Eriksen typically has a thickness of about 1000 Angstroms (column 4, lines 37-38) and thus cannot be said to be a self-supporting layer, as claimed.

Notably, oxide layer 6 is damaged during ion implantation in the Eriksen process, thus having to be stripped using an etch (column 4, lines 62-66), which of course can be avoided in the present invention as claimed, as can the subsequent cleaning required after etching (see column 4, lines 66-67 of Eriksen).

Accordingly, as nothing in Eriksen discloses or suggests the presently claimed process Applicants respectfully request the reconsideration and withdrawal of the outstanding rejection, and the passage of this case to Issue.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.

Richard L. Treanor
Attorney of Record
Registration No. 36,379

Customer Number
22850

Tel: (703) 413-3000
Fax: (703) 413 -2220
(OSMMN 08/07)